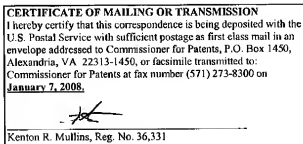


**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Applications of: /  
MACRONIX INTERNATIONAL CO., LTD. /  
U.S. Serial No: Listed on attached /  
Filed: Listed on attached /  
Re: Revocation of Power of Attorney with /  
New Power of Attorney and Change of /  
Correspondence Address and Statcment /  
Under 37 C.F.R. 3.73(b) /

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450



**TRANSMITTAL**

Sir:

Submitted herewith are:

- (1) Revocation of Power of Attorney with New Power of Attorney and Change of Correspondence Address and Statement Under 37 C.F.R. 3.73(b); and
- (2) Deposit Account Authorization: The Commissioner is hereby authorized to charge any needed fees to deposit account 50-1600.

Respectfully submitted,



Kenton R. Mullins  
Registration No. 36,331

January 7, 2008

STOUT, UXA, BUYAN & MULLINS, LLP  
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Irvine, CA 92618  
Tel: 949-450-1750  
Fax: 949-450-1764

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

### REVOCATION OF POWER OF ATTORNEY WITH NEW POWER OF ATTORNEY AND CHANGE OF CORRESPONDENCE ADDRESS AND STATEMENT UNDER 37 C.F.R. 3.73(b)

Sir:


MACRONIX INTERNATIONAL CO., LTD., a corporation, states that it is the assignee of record of the entire right, title and interest of the below-identified patent applications by virtue of assignment from inventor(s) to assignee. I hereby revoke all previous powers of attorney given in the applications identified below and hereby appoint the practitioners associated with:

**Customer No.: 33197.**

A chain of title from the inventor(s) to the current assignee is shown below:

#### Patent Applications

U.S. Patent Appln. No.	Filing Date	Title	Inventor(s)	Assignment Recorded from Inventor(s) to Assignee MACRONIX INTERNATIONAL CO., LTD. At Reel/ Frame
10/189,084	2002/7/3	Security Memory Device and Method for Making Same	LI, MINFU et al.	P90059USA.pdf for which a copy thereof is attached
10/719,759	2003/11/20	Method of improving thermal stability for cobalt salicide	SU, CHIN-TA	014742/0715
10/872,086	2004/6/17	Methods for sidewall etching and etching during filling of a trench	LIU, YUH-TUNG	015501/0414
10/948,891	2004/9/24	Chalcogenide memory	CHEN, YI CHOU	015831/0867
11/881,077	2007/7/24	Structure for phase change memory and the method of forming same	LEE, MING HSIU et al.	CA of US 10/966,335 (015905/0300)
11/123,589	2005/5/6	Buried Bit Line Anti-Fuse One-Time-Programmable Nonvolatile Memory	LUNG, HSIANG-LAN	016863/0976
11/134,155	2005/5/20	Air tunnel floating gate	LUE, HANG-TING et	016589/0306

		memory cell and method for making the same	al.	
11/218,806	2005/9/2	Self-adjusting clock generator with stable frequency output	TSENG, CHIEN-CHUNG	017268/0198
11/250,959	2005/10/14	Nitride read only memory device with buried diffusion spacers and method for making the same	LIU, CHIEN HUNG	017102/0270
11/255,761	2005/10/21	Method to prevent anti-assist feature and side lobe from printing out	YANG, CHIN CHENG	017123/0737
11/255,791	2005/10/21	Method to form photo patterns	YANG, CHIN CHENG	017138/0981
11/285,919	2005/11/23	NAND Type Multi-Bit Charge Storage Memory Array and Methods for Operating and Fabricating the Same	CHEN, YIN JEN et al.	017276/0621
11/399,770	2006/4/7	Method for forming self-aligned contacts and local interconnects simultaneously	LUOH, TUUNG et al.	017771/0484
11/027,807	2004/12/30	High Aspect-Ratio PN-Junction and Method for Manufacturing the Same	WU, CHAO-I et al.	016157/0573
11/750,296	2007/5/17	METHOD FOR NROM ARRAY WORD LINE RETRY ERASING AND THRESHOLD VOLTAGE RECOVERING	HUNG, CHUN-HSIUNG et al.	<div data-bbox="699 954 906 993" data-label="Text"> <p>  <a href="#">D:\470090101\152_5.PDF</a> </p> </div> <p>for which a copy thereof is attached</p>
11/420,930	2006/5/30	Magnetic Random Access Memory Using Single Crystal Self-aligned Diode	HO, CHIAHUA et al.	018384/0654

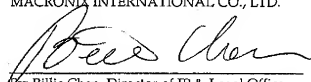
I am empowered to act on behalf of the assignee.

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon .

Respectfully submitted,

MACRONIX INTERNATIONAL CO., LTD.

Date: JAN - 3 2008

  
By: Billie Chen, Director of IP & Legal Office  
MACRONIX INTERNATIONAL CO., LTD.